mail

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



US-Lasers: 780nm-5mW - Infrared Laser Diodes and Infrared Diode Laser Modules

Back to Laser Modules

TECHNICAL DATA for LASER MODULE						
Barrel Specs:	Collect Specs:	Lens Housing Specs:				
 3/8 - 56 Thread Size Dia: 10.4mm Length: 17mm 	 3/8 - 56 Thread Size 4.3mm Aperature Half Hard Brassbbb 	 3/8 - 56 Thread Size 3.7mm Aperture 7mm Plastic Lens 				

INFRARED DIODE LASER DATA SHEETS

ABSOLUTE MAXIMUM RATINGS - (Tc=25 °C)

TECHNICAL DATA Index Guided MQW Structure Wavelength: 780nm (Typ.) Optical Power: 5mW CW Threshold Current: 25mA (Typ.) Standard Package: 5.6mm 				1 laser cathode 2 common case 3 monitor diode anode			
Infrared light output	780nm	780nm			Pin Out Diagram - Style A		
Optical power output	5mW CW	5mW CW				•	
Package Type	5.6mm	5.6mm					
Built-in photo diode for monitoring la							
Items	1		Symbols		Values	Unit	
Optical output power			Po		5	mW	
Laser diode reverse voltage			VLDR		2	V	
Photo diode reverse voltage			VPDR	30 V			
Operating temperature			Topr	-10 ~ +40 °C			
Storage temperature			Tstg		-40 ~ +85	°C	
OPTICAL and ELECTRICAL CHARACTERISTICS - (Tc=25 °C)							
Items	Symbols	Min.	Тур.	Max.	Unit	Test Condition	
Optical output power	Po	-	5	-	mW	-	
Threshold current	Ith	15	25	40	mA	-	
Operating current	Iop	25	35	50	mA	Po=5mW	
Operating voltage	Vop	1.9	2.1	2.5	V	Po=5mW	
Lasing wavelength	8 D	770	780	790	nm	Po=5mW	
Beam divergence	θF	8	11	15	deg	Po=5mW	
Beam divergence	θz	20	35	45	deg	Po=5mW	
Slope Efficiency (mW/mA)	0	0.1	0.3	0.6		-	
Monitor current	Im	100	200	600	μΑ	Po=5mW,Vr=5V	
Astigmatism	As	-	11	-	μm	Po=5mW	
MTTF			3000-5,000 hrs.			Po=5mW,NA=0.4	
Emitter Size	1 x 4 Microns						
Emitter Distance to Cap Lens	0.3mm						
Structure	Index Guided						